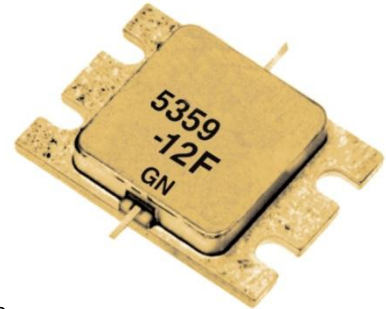


FEATURES

- High Output Power: $P_{1dB} = 41.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 9.5\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 38\%$ (Typ.)
- Low IM3: $-46\text{dBc@Po} = 30.5\text{dBm}$
- Broad Band: 5.3 to 5.9GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\text{ohm}$



DESCRIPTION

The FLM5359-12F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

SEDI's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25\text{deg.C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25\text{deg.C}$	57.6	W
Storage Temperature	T_{stg}		-65 to +175	deg.C
Channel Temperature	T_{ch}		175	deg.C

SEDI recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 32.0 and -5.6 mA respectively with gate resistance of 50ohm.

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25\text{deg.C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS}=5V, V_{GS}=0V$	-	5800	8700	mA
Transconductance	g_m	$V_{DS}=5V, I_{DS}=3400\text{mA}$	-	2900	-	mS
Pinch-off Voltage	V_p	$V_{DS}=5V, I_{DS}=300\text{mA}$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS}=-300\mu A$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS}=10V,$	40.5	41.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}	$I_{DS}=0.55 I_{DSS}$ (Typ.),	8.5	9.5	-	dB
Drain Current	I_{dsr}	$f=5.3$ to 5.9 GHz,	-	3250	3800	mA
Power-added Efficiency	η_{add}	$Z_S=Z_L=50\text{ohm}$	-	38	-	%
Gain Flatness	ΔG		-	-	+/-0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 5.9$ GHz, $\Delta f = 10$ MHz 2-Tone Test $P_{out} = 30.5\text{dBm S.C.L.}$	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	2.3	2.6	deg.C/W
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{dsr} \times R_{th}$	-	-	80	deg.C

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

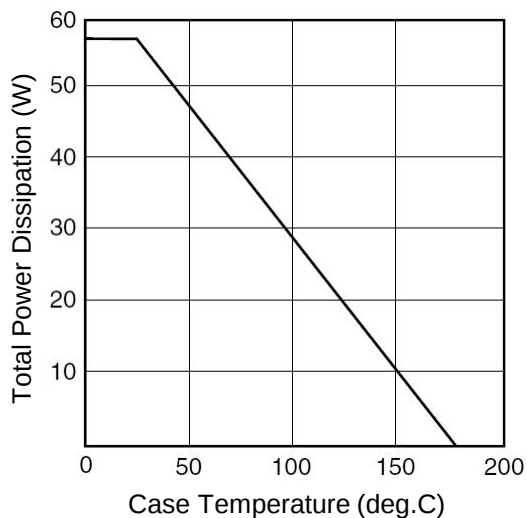
CASE STYLE	IK
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ESD	Class 3A	4000V to 8000V
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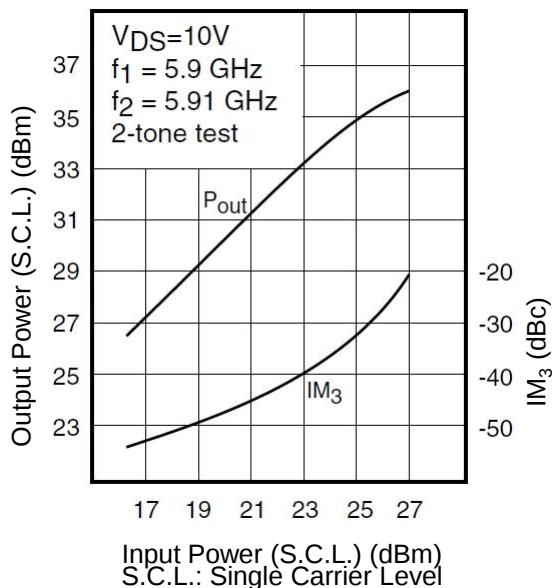
Note : Based on EIAJ ED-4701 C-111A (C=100pF, R=1.5kohm)

RoHS Compliance	Yes
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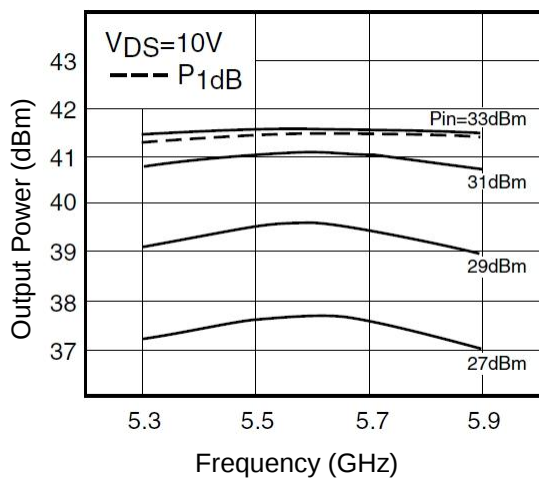
POWER DERATING CURVE



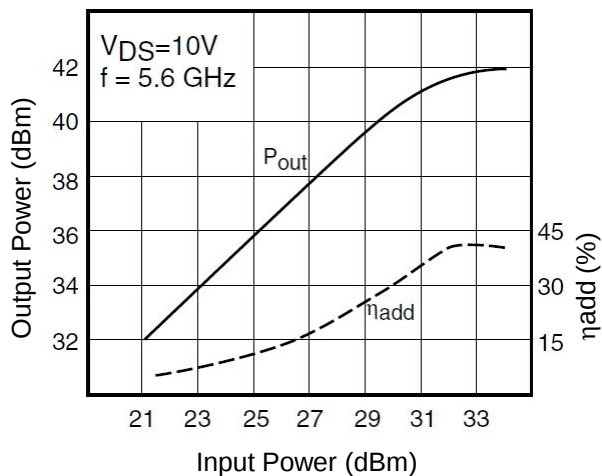
OUTPUT POWER & IM₃ vs. INPUT POWER

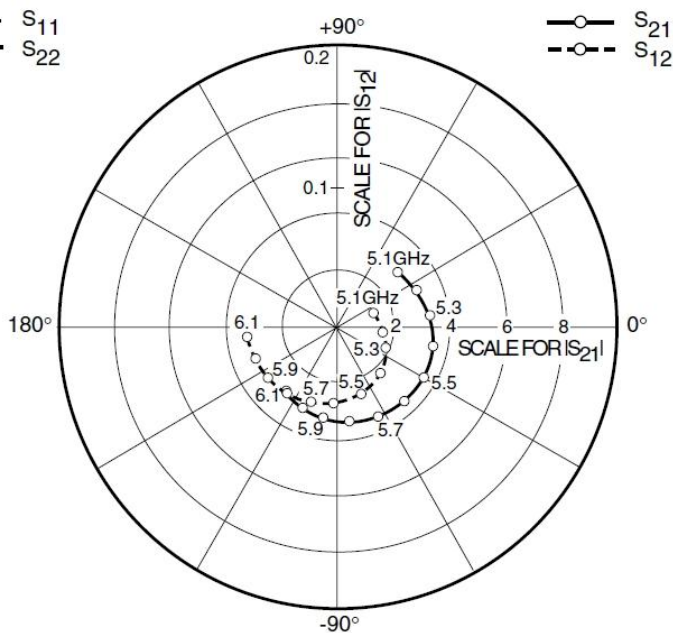
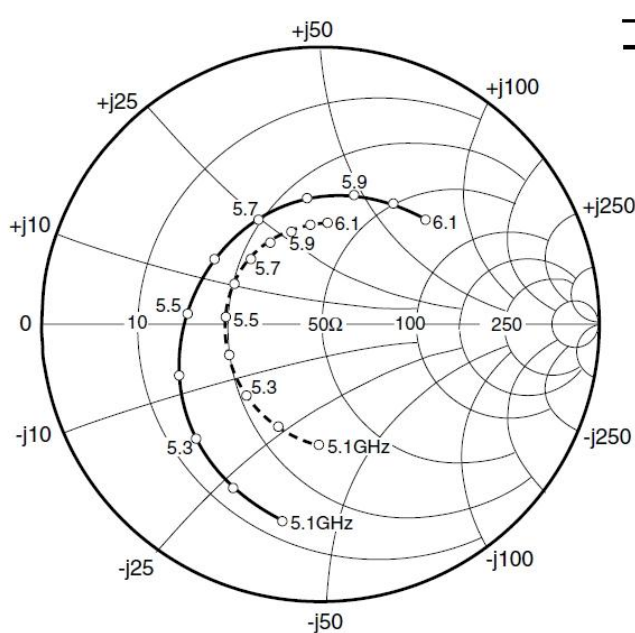


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER



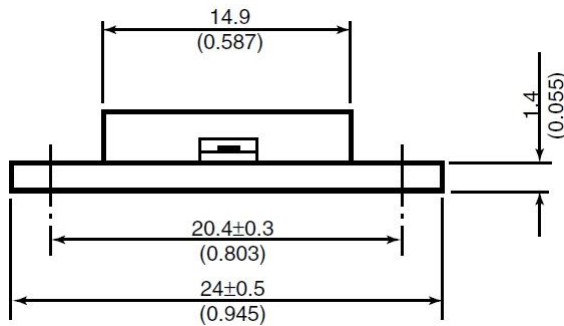
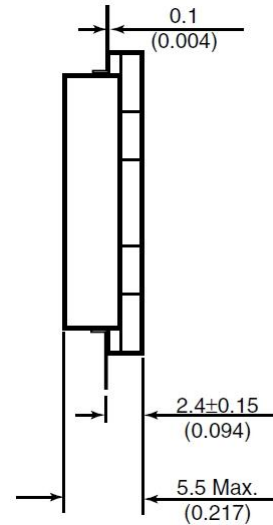
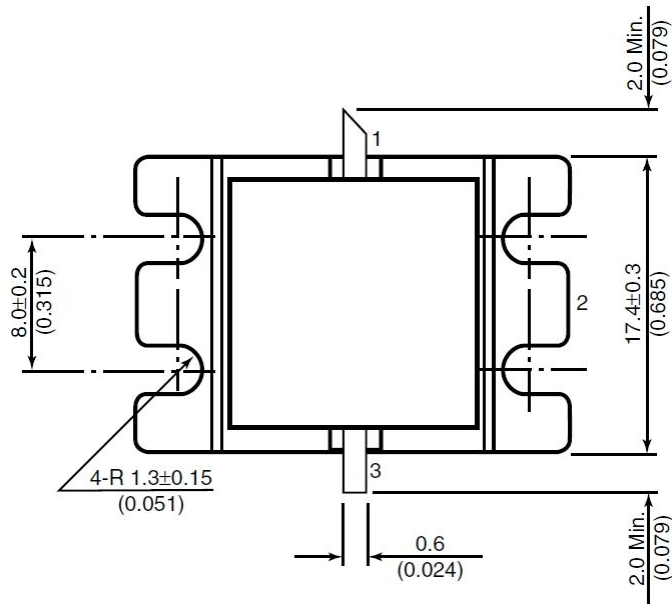


S-PARAMETERS

V_{DS} = 10V, I_{DS} = 3400mA

FREQUENCY (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
5100	0.722	-100.8	2.867	43.0	0.027	21.1	0.434	-91.7
5200	0.670	-118.0	3.100	25.4	0.031	-4.1	0.401	-113.1
5300	0.608	-137.4	3.299	7.2	0.038	-26.3	0.372	-136.6
5400	0.543	-159.6	3.429	-11.6	0.044	-49.2	0.352	-161.0
5500	0.485	175.3	3.497	-30.0	0.050	-71.0	0.343	175.8
5600	0.448	148.0	3.502	-48.4	0.054	-91.6	0.344	155.0
5700	0.441	120.7	3.449	-66.1	0.057	-110.3	0.344	137.0
5800	0.458	96.4	3.357	-83.2	0.060	-128.1	0.346	121.8
5900	0.485	76.0	3.250	-99.5	0.063	-144.4	0.350	108.2
6000	0.513	59.3	3.141	-114.9	0.064	-159.7	0.357	96.8
6100	0.536	45.2	3.053	-129.7	0.066	-174.1	0.365	86.8

Case Style "IK"
Metal-Ceramic Hermetic Package



1. Gate
2. Source (Flange)
3. Drain

Unit: mm(inches)

For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>

CAUTION

This product contains **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.